

## N-Channel 150 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY		
V <sub>DS</sub> (V)	R <sub>DS(on)</sub> (Ω)	I <sub>D</sub> (A)
150	0.095 at V <sub>GS</sub> = 10 V	15
	0.100 at V <sub>GS</sub> = 6 V	15

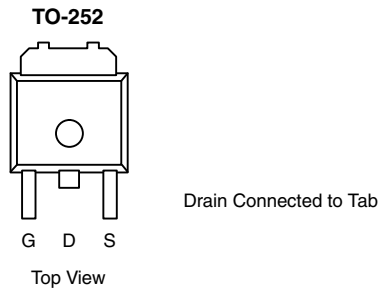
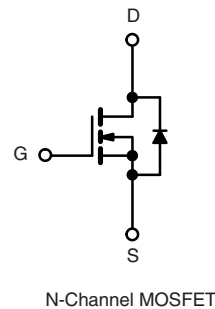
### FEATURES

- TrenchFET<sup>®</sup> Power MOSFETS
- 175 °C Junction Temperature
- 100 % R<sub>g</sub> Tested
- Material categorization: For definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)


**RoHS**  
COMPLIANT

### APPLICATIONS

- Primary Side Switch


**Ordering Information:** SUD15N15-95-E3 (Lead (Pb) free)


ABSOLUTE MAXIMUM RATINGS (T <sub>C</sub> = 25 °C, unless otherwise noted)			
Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V <sub>DS</sub>	150	V
Gate-Source Voltage	V <sub>GS</sub>	± 20	
Continuous Drain Current (T <sub>J</sub> = 175 °C) <sup>b</sup>	I <sub>D</sub>	T <sub>C</sub> = 25 °C	15
		T <sub>C</sub> = 125 °C	8.7
Pulsed Drain Current	I <sub>DM</sub>	25	A
Continuous Source Current (Diode Conduction)	I <sub>S</sub>	15	
Avalanche Current	I <sub>AR</sub>	15	
Repetitive Avalanche Energy (Duty Cycle ≤ 1 %)	L = 0.1 mH E <sub>AR</sub>	11.3	mJ
Maximum Power Dissipation	P <sub>D</sub>	T <sub>C</sub> = 25 °C	62 <sup>b</sup>
		T <sub>A</sub> = 25 °C	2.7 <sup>a</sup>
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	- 55 to 175	°C

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Typical	Maximum	Unit	
Junction-to-Ambient <sup>a</sup>	R <sub>thJA</sub>	t ≤ 10 s	16	20	°C/W
		Steady State	45	55	
Junction-to-Case	R <sub>thJC</sub>	2	2.4		

Notes:

a. Surface mounted on 1" x 1" FR4 board.

b. See SOA curve for voltage derating.

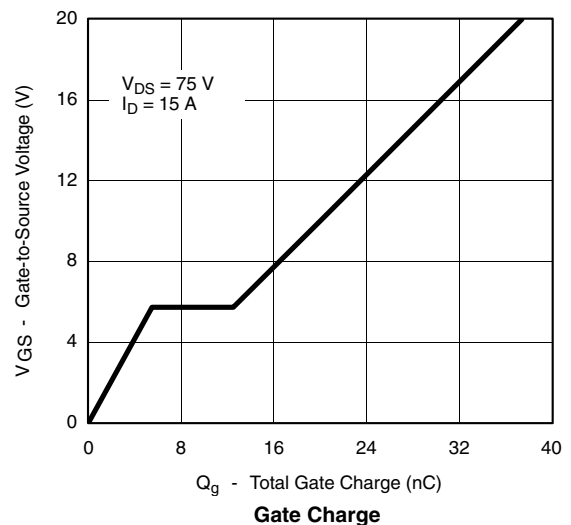
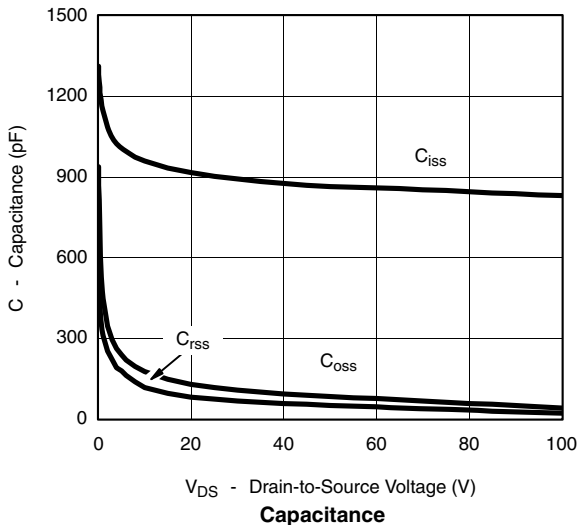
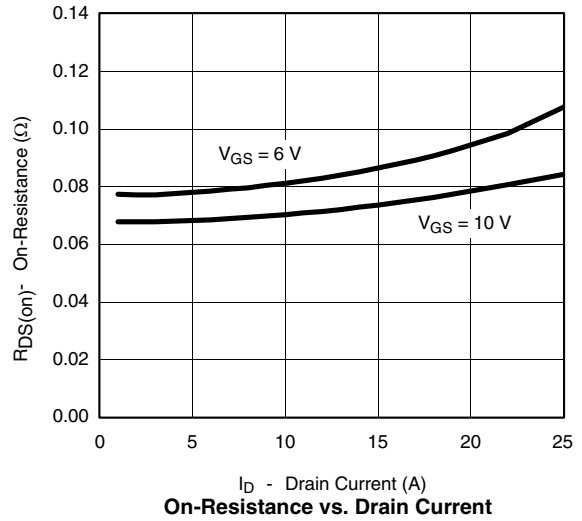
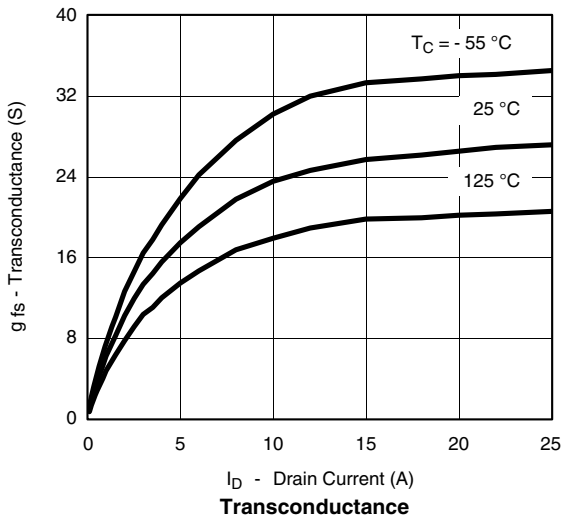
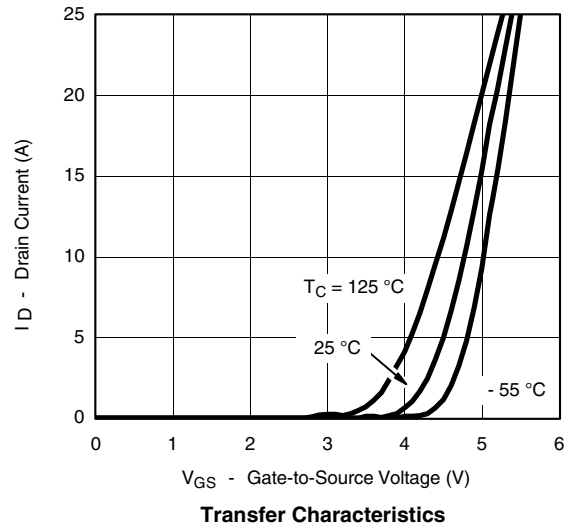
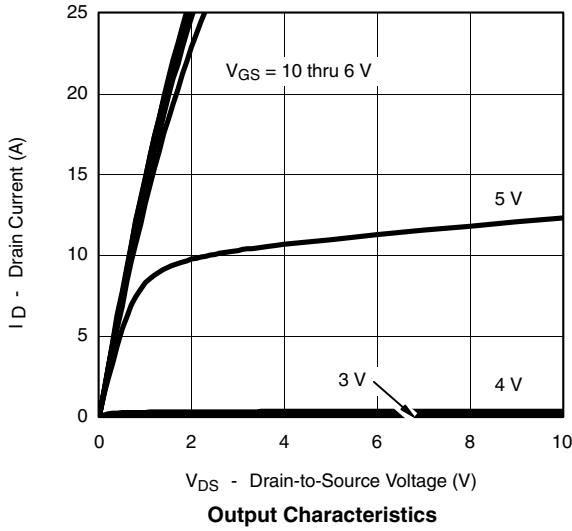
<b>SPECIFICATIONS</b> ( $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min.	Typ. <sup>a</sup>	Max.	Unit
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	150			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	2			
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 120\text{ V}, V_{GS} = 0\text{ V}$			1	$\mu\text{A}$
		$V_{DS} = 120\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$			50	
		$V_{DS} = 120\text{ V}, V_{GS} = 0\text{ V}, T_J = 175\text{ }^\circ\text{C}$			250	
On-State Drain Current <sup>b</sup>	$I_{D(on)}$	$V_{DS} = 5\text{ V}, V_{GS} = 10\text{ V}$	25			A
Drain-Source On-State Resistance <sup>b</sup>	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 15\text{ A}$		0.077	0.095	$\Omega$
		$V_{GS} = 10\text{ V}, I_D = 15\text{ A}, T_J = 125\text{ }^\circ\text{C}$			0.190	
		$V_{GS} = 10\text{ V}, I_D = 15\text{ A}, T_J = 175\text{ }^\circ\text{C}$			0.250	
		$V_{GS} = 6\text{ V}, I_D = 10\text{ A}$		0.081	0.100	
Forward Transconductance <sup>b</sup>	$g_{fs}$	$V_{DS} = 15\text{ V}, I_D = 15\text{ A}$		25		S
<b>Dynamic<sup>a</sup></b>						
Input Capacitance	$C_{iss}$	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$		900		$\text{pF}$
Output Capacitance	$C_{oss}$			115		
Reverse Transfer Capacitance	$C_{rss}$			70		
Total Gate Charge <sup>c</sup>	$Q_g$	$V_{DS} = 75\text{ V}, V_{GS} = 10\text{ V}, I_D = 15\text{ A}$		20	25	$\text{nC}$
Gate-Source Charge <sup>c</sup>	$Q_{gs}$			5.5		
Gate-Drain Charge <sup>c</sup>	$Q_{gd}$			7		
Gate Resistance	$R_g$		1		3.2	$\Omega$
Turn-On Delay Time <sup>c</sup>	$t_{d(on)}$	$V_{DD} = 75\text{ V}, R_L = 5\text{ }\Omega$ $I_D \cong 15\text{ A}, V_{GEN} = 10\text{ V}, R_G = 2.5\text{ }\Omega$		8	12	ns
Rise Time <sup>c</sup>	$t_r$			35	55	
Turn-Off Delay Time <sup>c</sup>	$t_{d(off)}$			17	25	
Fall Time <sup>c</sup>	$t_f$			30	45	
<b>Source-Drain Diode Ratings and Characteristic</b> ( $T_C = 25\text{ }^\circ\text{C}$ )						
Pulsed Current	$I_{SM}$				25	A
Diode Forward Voltage <sup>b</sup>	$V_{SD}$	$I_F = 15\text{ A}, V_{GS} = 0\text{ V}$		0.9	1.5	V
Source-Drain Reverse Recovery Time	$t_{rr}$	$I_F = 15\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$		55	85	ns

## Notes:

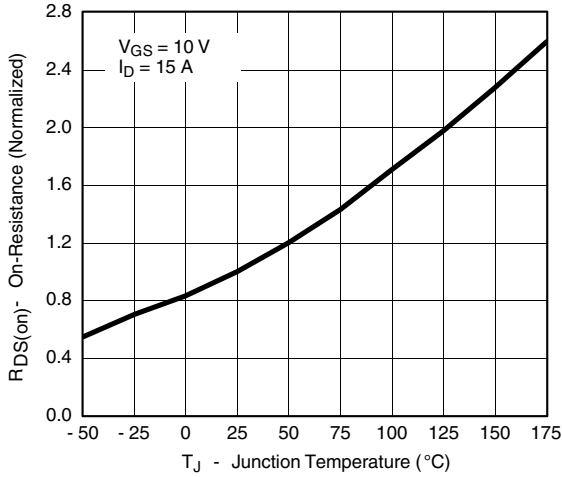
- Guaranteed by design, not subject to production testing.
- Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .
- Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

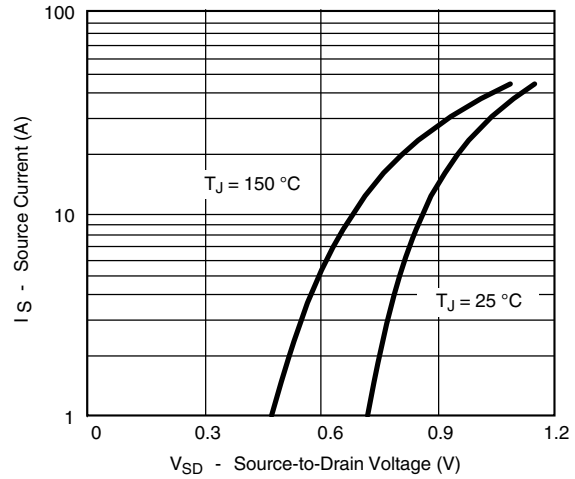
**TYPICAL CHARACTERISTICS** (25 °C unless noted)



### TYPICAL CHARACTERISTICS (25 °C unless noted)

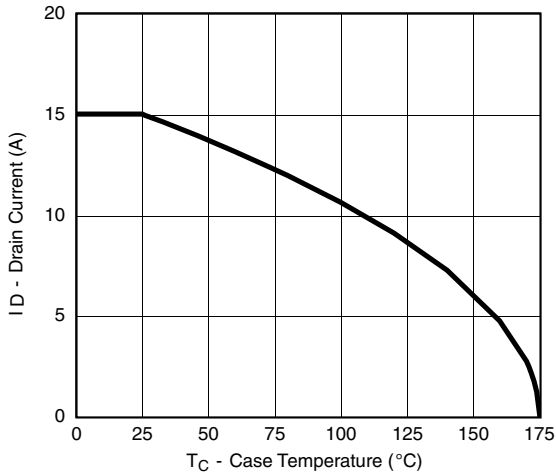


On-Resistance vs. Junction Temperature

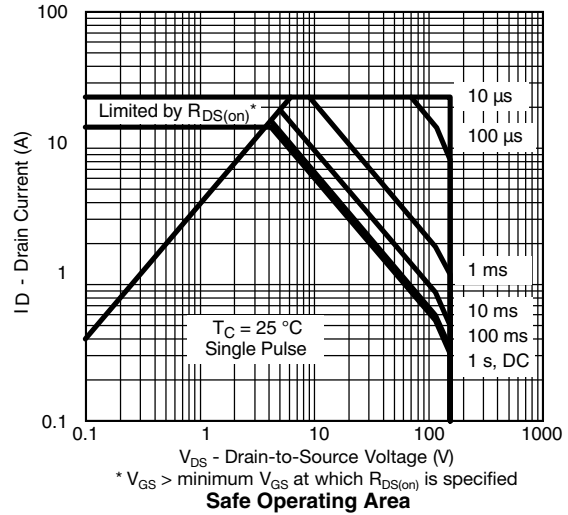


Source-Drain Diode Forward Voltage

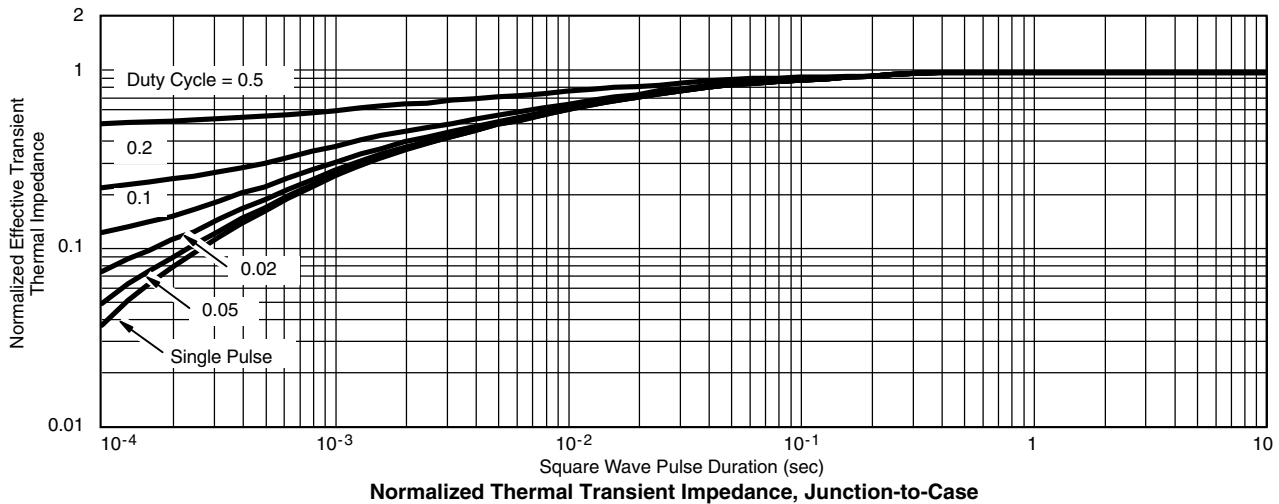
### THERMAL RATINGS



Maximum Avalanche Drain Current vs. Case Temperature



Safe Operating Area



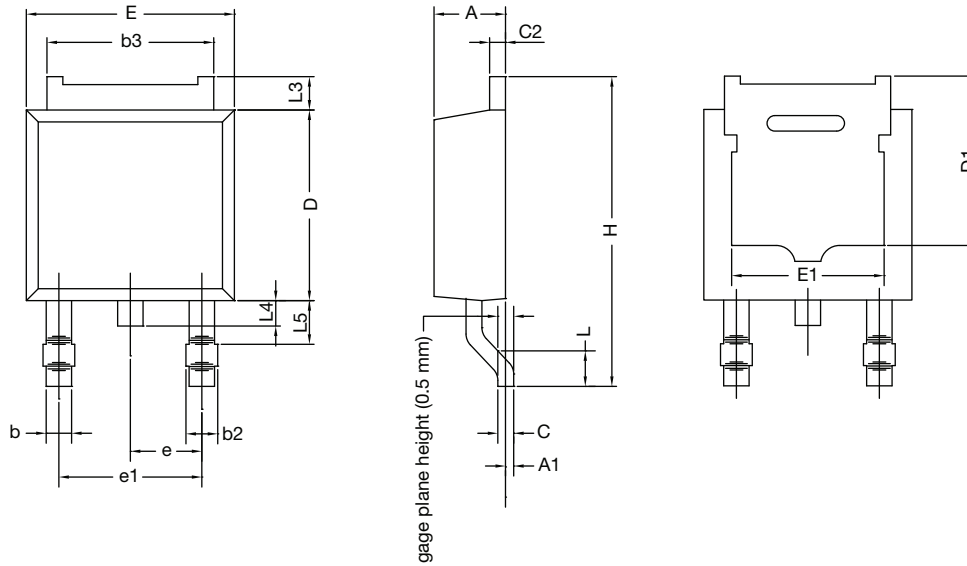
Normalized Thermal Transient Impedance, Junction-to-Case

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# TO-252AA Case Outline

## VERSION 1: FACILITY CODE = Y



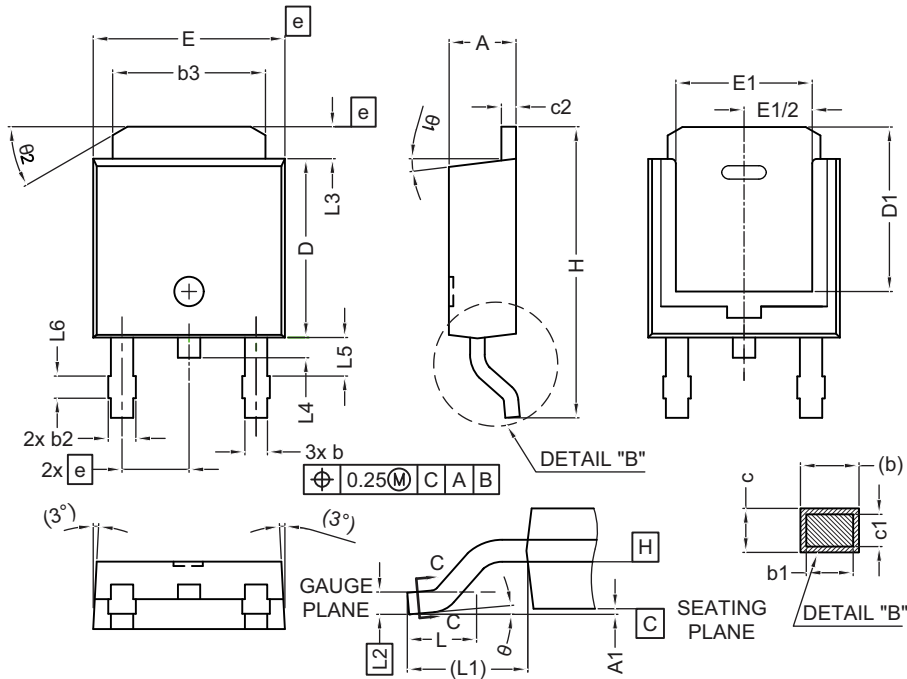
DIM.	MILLIMETERS	
	MIN.	MAX.
A	2.18	2.38
A1	-	0.127
b	0.64	0.88
b2	0.76	1.14
b3	4.95	5.46
C	0.46	0.61
C2	0.46	0.89
D	5.97	6.22
D1	4.10	-
E	6.35	6.73
E1	4.32	-
H	9.40	10.41
e	2.28 BSC	
e1	4.56 BSC	
L	1.40	1.78
L3	0.89	1.27
L4	-	1.02
L5	1.01	1.52

### Note

- Dimension L3 is for reference only



VERSION 2: FACILITY CODE = N



MILLIMETERS		
DIM.	MIN.	MAX.
A	2.18	2.39
A1	-	0.13
b	0.65	0.89
b1	0.64	0.79
b2	0.76	1.13
b3	4.95	5.46
c	0.46	0.61
c1	0.41	0.56
c2	0.46	0.60
D	5.97	6.22
D1	5.21	-
E	6.35	6.73
E1	4.32	-
e	2.29 BSC	
H	9.94	10.34

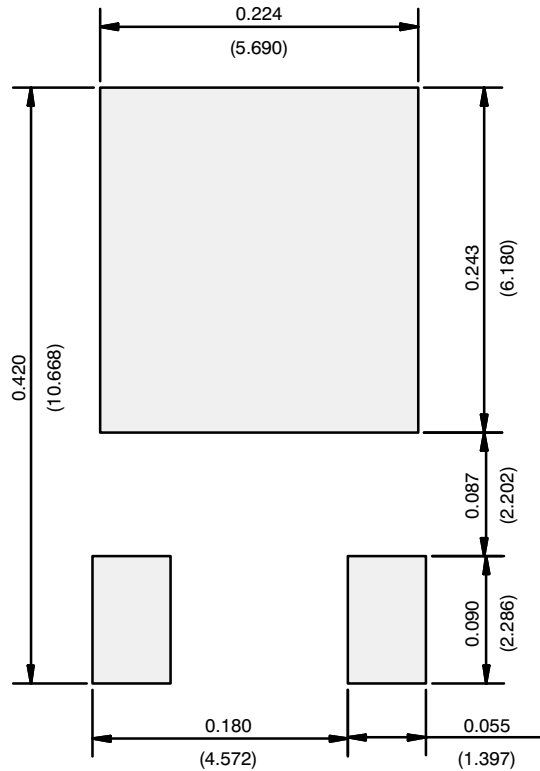
MILLIMETERS		
DIM.	MIN.	MAX.
L	1.50	1.78
L1	2.74 ref.	
L2	0.51 BSC	
L3	0.89	1.27
L4	-	1.02
L5	1.14	1.49
L6	0.65	0.85
θ	0°	10°
θ1	0°	15°
θ2	25°	35°

Notes

- Dimensioning and tolerance confirm to ASME Y14.5M-1994
- All dimensions are in millimeters. Angles are in degrees
- Heat sink side flash is max. 0.8 mm
- Radius on terminal is optional

ECN: E19-0649-Rev. Q, 16-Dec-2019  
 DWG: 5347

## RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads  
Dimensions in Inches/(mm)

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